ESD/Surge Protection Diode Array

Bi-directional ESD Protection for High-Speed Data Line

SMDA05C Series

The SMDA05C surge protection series is designed to protect equipment attached to up to four high speed communication lines from ESD, EFT and surge.

Features

- SO-8 Package
- Peak Power 300 W 8 x 20 μs
- ESD Rating: IEC 61000-4-2 (ESD) ±15 kV (Air) ±8 kV (Contact) IEC 61000-4-4 (EFT) 40 A (5/50 ns) IEC 61000-4-5 (Surge) 12 A (8/20 μs)
- UL Flammability Rating of 94 V-0
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- High Speed Communication Line Protection
- Data and I/O Lines
- Microprocessor Based Equipment
- LAN/WAN Equipment
- Servers
- Notebook and Desktop PC
- Serial and Parallel Ports
- Peripherals

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------------------------------|-----------------|------|
| Peak Power Dissipation 8 x 20 μ s @ T _A = 25°C (Note 1) | P _{pk} | 300 | W |
| Junction and Storage Temperature Range | T _J , T _{stg} | – 55 to +150 | °C |
| Lead Solder Temperature – Maximum 10 Seconds Duration | ΤL | 260 | °C |

1. Non-repetitive current pulse 8 x 20 μs exponential decay waveform.

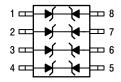


ON Semiconductor®

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SO-8 ESD AND SURGE PROTECTOR 300 WATTS PEAK POWER

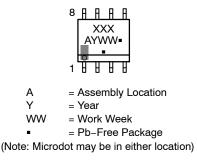






SO-8 CASE 751-07

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 3 of this data sheet.

SMDA05C Series

SMDA05C ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|------------------|-----|-----|-----|------|
| Reverse Working Voltage | V _{RWM} | - | - | 5.0 | V |
| Reverse Breakdown Voltage @ I _t = 1.0 mA | V _{BR} | 6.0 | - | - | V |
| Reverse Leakage Current @ V _{RWM} = 5 Volts | I _R | N/A | - | 20 | μA |
| Maximum Clamping Voltage @ I_{PP} = 1.0 A, 8 x 20 μ s | V _C | N/A | - | 9.8 | V |
| Maximum Clamping Voltage @ I_{PP} = 5.0 A, 8 x 20 μ s | V _C | N/A | - | 11 | V |
| Maximum Peak Pulse Current, 8 x 20 μ s | I _{PP} | - | - | 17 | Α |
| Junction Capacitance @ V_R = 0 V, f = 1 MHz | CJ | - | - | 350 | pF |

SMDA12C ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|------------------|------|-----|-----|------|
| Reverse Working Voltage | V _{RWM} | - | - | 12 | V |
| Reverse Breakdown Voltage @ $I_t = 1.0 \text{ mA}$ | V _{BR} | 13.3 | - | - | V |
| Reverse Leakage Current @ V _{RWM} = 12 Volts | I _R | N/A | - | 1.0 | μΑ |
| Maximum Clamping Voltage @ I _{PP} = 1.0 A, 8 x 20 μs | V _C | N/A | - | 19 | V |
| Maximum Clamping Voltage @ I _{PP} = 5.0 A, 8 x 20 μs | V _C | N/A | - | 24 | V |
| Maximum Peak Pulse Current, 8 x 20 μs | I _{PP} | - | - | 12 | A |
| Junction Capacitance @ V _R = 0 V, f = 1 MHz | CJ | - | - | 120 | pF |

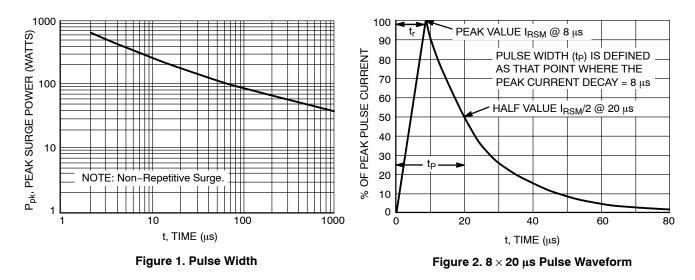
SMDA15C ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|------------------|------|-----|-----|------|
| Reverse Working Voltage | V _{RWM} | - | - | 15 | V |
| Reverse Breakdown Voltage @ I _t = 1.0 mA | V _{BR} | 16.7 | - | - | V |
| Reverse Leakage Current @ V _{RWM} = 15 Volts | I _R | N/A | - | 1.0 | μΑ |
| Maximum Clamping Voltage @ I _{PP} = 1.0 A, 8 x 20 μs | V _C | N/A | - | 24 | V |
| Maximum Clamping Voltage @ I_{PP} = 5.0 A, 8 x 20 μs | V _C | N/A | - | 30 | V |
| Maximum Peak Pulse Current, 8 x 20 μs | I _{PP} | - | - | 10 | А |
| Junction Capacitance @ $V_R = 0 V$, f = 1 MHz | CJ | - | - | 75 | pF |

SMDA24C ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|------------------|------|-----|-----|------|
| Reverse Working Voltage | V _{RWM} | - | - | 24 | V |
| Reverse Breakdown Voltage @ I _t = 1.0 mA | V _{BR} | 26.7 | - | - | V |
| Reverse Leakage Current @ V _{RWM} = 24 Volts | I _R | N/A | - | 1.0 | μA |
| Maximum Clamping Voltage @ I_{PP} = 1.0 A, 8 x 20 μ s | V _C | N/A | - | 43 | V |
| Maximum Clamping Voltage @ I_{PP} = 5.0 A, 8 x 20 μ s | V _C | N/A | - | 55 | V |
| Maximum Peak Pulse Current, 8 x 20 μs | I _{PP} | - | - | 5.0 | A |
| Junction Capacitance @ V _R = 0 V, f = 1 MHz | CJ | - | - | 50 | pF |

SMDA05C Series



ORDERING INFORMATION

| Device | Marking | Package | Shipping [†] |
|-------------|---------|-------------------|-----------------------|
| SMDA05CDR2G | AAA | SO–8 (Pb–Free) | 2500 / Tape & Reel |
| SMDA12CDR2G | AAC | SO-8 (Pb-Free) | 2500 / Tape & Reel |
| SMDA15CDR2G | AAD | SO–8 (Pb–Free) | 2500 / Tape & Reel |
| SMDA24CDR2G | AAE | SO-8 (Pb-Free) | 2500 / Tape & Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR З. 4. EMITTER EMITTER 5. 6. BASE 7 BASE 8. EMITTER STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. 5. GATE 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6. BASE, DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. 4. TXE 5. RXE 6. VFF GND 7. 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 З. CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C З. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. EMITTER, #1 BASE, #2 2. З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 З. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND BIAS 2 INPUT 6. 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. 5. P-DRAIN 6. P-DRAIN N-DRAIN 7. 8. N-DRAIN STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC I/O LINE 3 4. 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt ENABLE З. 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: PIN 1. DRAIN 1 DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

| STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 |
|---|
| STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd |
| STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 7. DRAIN 1 8. DRAIN 1 |
| STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON |
| STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 |
| STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT |
| STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN |

DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER З. COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE CATHODE COLLECTOR/ANODE 6. 7. COLLECTOR/ANODE 8. STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

8

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COLLECTOR, #1

COLLECTOR, #1

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